

## TSDxxC Bidirectional TVS Diodes in SOD-323 Package

### 1 Features

- IEC 61000-4-2 ESD protection:
  - $\pm 30\text{kV}$  contact discharge
  - $\pm 30\text{kV}$  air gap discharge
- IEC 61000-4-5 surge protection:
  - 6.5-30A (8/20 $\mu\text{s}$ )
- Low IO capacitance < 4.5pF
- Ultra low leakage current: 10nA (maximum)
- Industrial temperature range:  $-55^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$
- Industry standard SOD-323 leaded package (2.5mm  $\times$  1.3mm)

### 2 Applications

- I/O Protection
- Power Line Protection
- [USB VBUS](#)
- [Appliances](#)
- [Medical & Healthcare](#)
- [Retail Automation](#)

### 3 Description

The TSDxxC are a family of bidirectional TVS protection diodes designed for clamping harmful transients such as ESD and surge. The TSDxxC devices are rated to dissipate ESD strikes up to  $\pm 30\text{kV}$  (contact and air gap discharge) which exceeds the maximum level specified in the IEC 61000-4-2 international standard (Level 4).

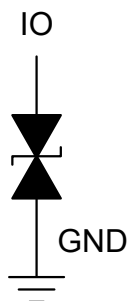
Combining the robust clamping performance and low capacitance of these devices, TSDxxC are excellent TVS diodes to protect both data lines and power lines in many different applications.

The TSDxxC family is offered in the industry standard, leaded SOD-323 package to enable easy solderability.

#### Package Information

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
TSDxxC	DYF (SOD-323, 2)	2.65mm $\times$ 1.3mm

- (1) For more information, see [Section 9](#).
- (2) The package size (length  $\times$  width) is a nominal value and includes pins, where applicable.



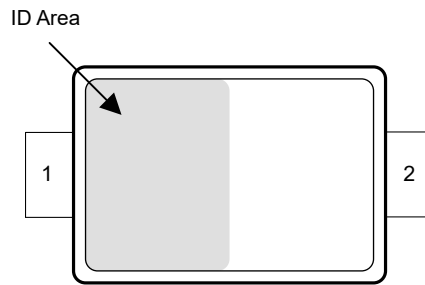
Functional Block Diagram



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## 4 Pin Configuration and Functions



**Figure 4-1. DYF Package, 2-Pin SOD-323 (Top View)**

**Table 4-1. Pin Functions**

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NO.	NAME		
1	IO	I/O	Protected Channel. If used as IO, connect pin 2 to ground
2	IO	I/O	Protected Channel. If used as IO, connect pin 1 to ground

(1) I = input, O = output

## 5 Specifications

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) <sup>(1)</sup>

Parameter		DEVICE	MIN	MAX	UNIT
$P_{PP}$ <sup>(2)</sup>	IEC 61000-4-5 ( $t_p$ 8/20 $\mu$ s) Peak Pulse Power at 25°C			400	W
$I_{PP}$	IEC 61000-4-5 ( $t_p$ 8/20 $\mu$ s) Peak Pulse Current at 25°C	TSD05C		30	A
$I_{PP}$	IEC 61000-4-5 ( $t_p$ 8/20 $\mu$ s) Peak Pulse Current at 25°C	TSD36C		6.5	A
$T_A$	Ambient Operating Temperature		-55	150	°C
$T_{stg}$	Storage Temperature		-65	155	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) Voltages are with respect to GND unless otherwise noted.

### 5.2 ESD Ratings—JEDEC Specification

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001 <sup>(1)</sup>	±2500	V
		Charged device model (CDM), per JEDEC specification JS-002 <sup>(2)</sup>	±1000	V

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

### 5.3 ESD Ratings—IEC Specification

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	IEC 61000-4-2 contact discharge	±30000	V
		IEC 61000-4-2 air-gap discharge	±30000	

### 5.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
T <sub>A</sub>	Operating free-air temperature	-55		150	°C

### 5.5 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TSD05C	TSD36C	UNIT
		DYF (SOD-323)	DYF (SOD-323)	
		2 PINS	2 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	672.0	686.1	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	230.5	267.0	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	541.4	560.5	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	64.4	91.4	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	527.5	546.2	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

### 5.6 Electrical Characteristics - TSD05C

At TA=25°C (unless otherwise noted) <sup>(1)</sup>

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
V <sub>RWM</sub>	Reverse stand-off voltage	I <sub>IO</sub> < 50nA, across operating temperature range	-5.5		5.5	V
V <sub>BR</sub>	Break-down voltage	I <sub>IO</sub> = 1mA, IO to GND and GND to IO	7	8	9	V
I <sub>LEAK</sub>	Reverse leakage current	V <sub>IO</sub> = 5.5V, IO to GND or GND to IO		5	10	nA
V <sub>CLAMP</sub>	Surge clamping voltage, t <sub>p</sub> = 8/20μs <sup>(2)</sup>	I <sub>PP</sub> = 24A, IO to GND or GND to IO		10.7	13.8	V
		I <sub>PP</sub> = 30 A, IO to GND or GND to IO		11.5	15	V
	TLP clamping voltage, t <sub>p</sub> = 100ns	I <sub>PP</sub> = 16 A, IO to GND or GND to IO		9.3		V
R <sub>DYN</sub>	Dynamic resistance <sup>(3)</sup>	IO to GND		0.15		Ω
		GND to IO				
C <sub>L</sub>	Line capacitance	V <sub>IO</sub> = 0V; f = 1 MHz, IO to GND		4	7	pF

(1) Typical parameters are measured at 25°C

(2) Nonrepetitive current pulse 8 to 20 μs exponentially decaying waveform according to IEC 61000-4-5

(3) Extraction of R<sub>DYN</sub> using least squares fit of TLP characteristics between I = 10 A and I = 20 A

## 5.7 Electrical Characteristics - TSD36C

At TA=25°C (unless otherwise noted) <sup>(1)</sup>

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
V <sub>RWM</sub>	Reverse stand-off voltage	I <sub>IO</sub> < 50nA, across operating temperature range			36	V
V <sub>BR</sub>	Breakdown voltage	I <sub>IO</sub> = 10mA, I/O to GND and GND to I/O	37.8	41.2	44.2	V
I <sub>LEAK</sub>	Reverse leakage current	V <sub>IO</sub> = 36V, IO to GND or GND to IO		5	10	nA
V <sub>CLAMP</sub>	Surge clamping voltage, t <sub>p</sub> = 8/20 μs <sup>(2)</sup>	I <sub>PP</sub> = 1A, IO to GND or GND to IO			47	V
		I <sub>PP</sub> = 5A, IO to GND or GND to IO			64	V
		I <sub>PP</sub> = 6.5A, IO to GND or GND to IO			71	V
	TLP clamping voltage, t <sub>p</sub> = 100ns	I <sub>PP</sub> = 16A, IO to GND or GND to IO		56		V
R <sub>DYN</sub>	Dynamic resistance <sup>(3)</sup>	IO to GND		0.6		Ω
		GND to IO				
C <sub>L</sub>	Line capacitance	V <sub>IO</sub> = 0V; f = 1MHz, IO to GND		4.3	6	pF

(1) Typical parameters are measured at 25°C

(2) Nonrepetitive current pulse 8 to 20μs exponentially decaying waveform according to IEC 61000-4-5

(3) Extraction of RDYN using least squares fit of TLP characteristics between I = 10A and I = 20A

## 5.8 Typical Characteristics

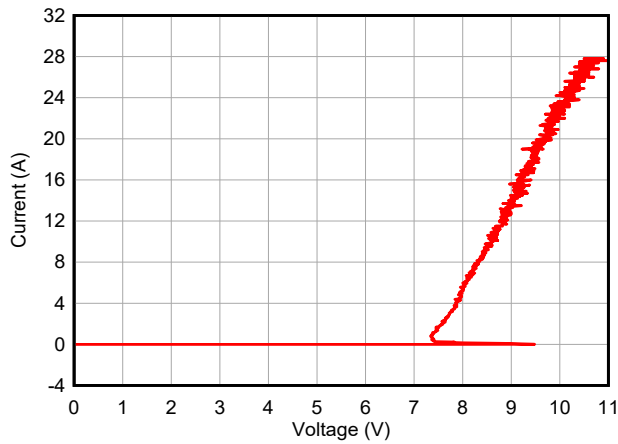


Figure 5-1. Positive TLP Curve - TSD05C

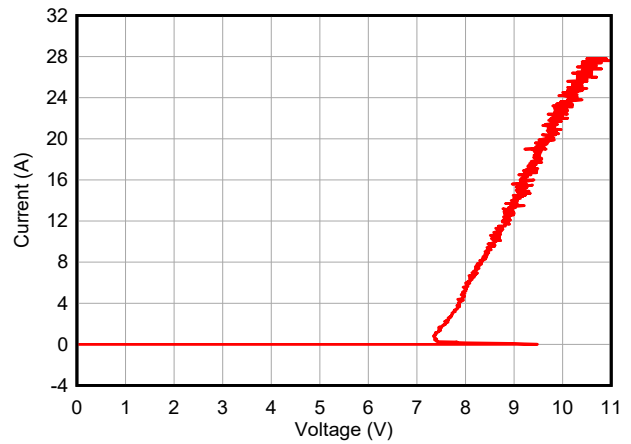


Figure 5-2. Negative TLP Curve - TSD05C

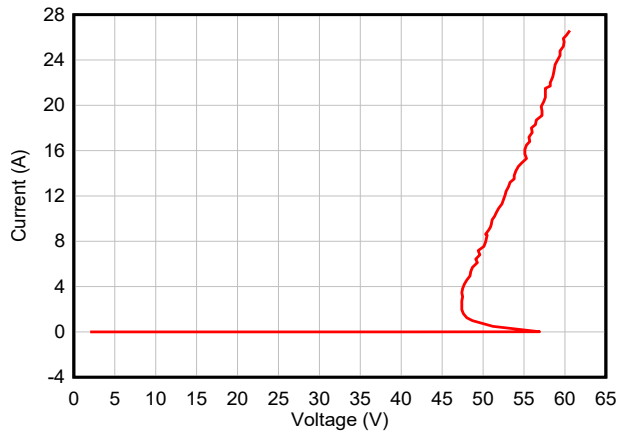


Figure 5-3. Positive TLP Curve - TSD36C

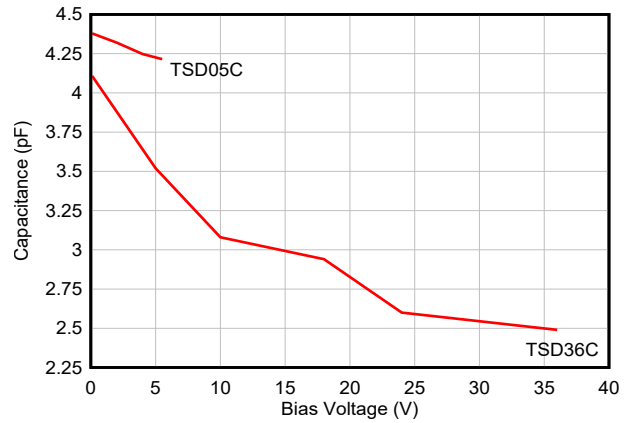


Figure 5-4. Capacitance vs Bias Voltage

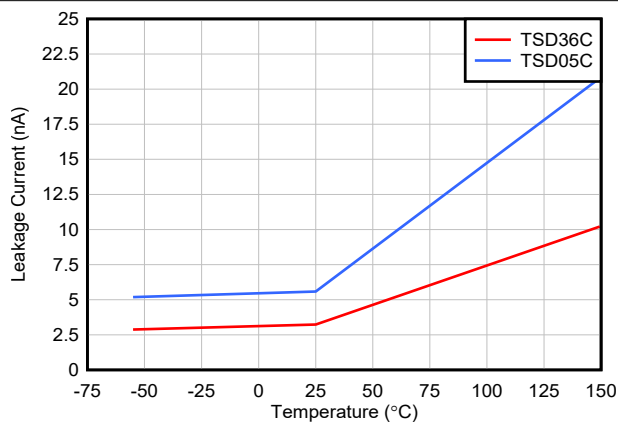


Figure 5-5. Leakage Current vs Temperature

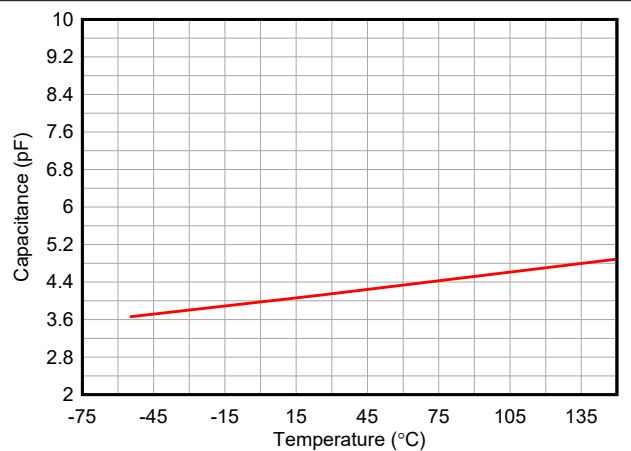
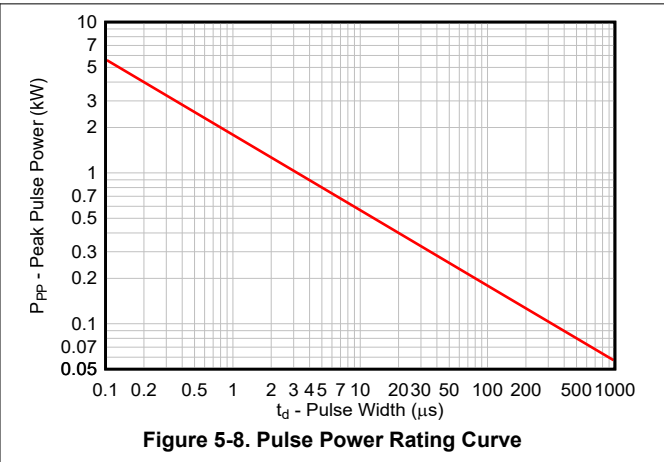
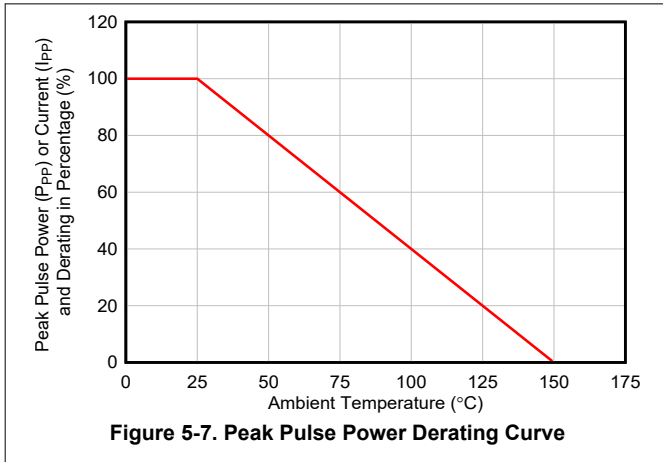


Figure 5-6. Capacitance vs Temperature - TSD05C

### 5.8 Typical Characteristics (continued)



## 6 Application and Implementation

### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 6.1 Application Information

The TSDxxC are TVS diodes that provide a path to ground for dissipating transient voltage spikes (such as ESD or surge) on signal lines and power lines. Connect the device in parallel to the down stream circuitry for protection. As the current from the transient passes through the TVS, only a small voltage drop is present across the diode. The small voltage drop is presented to the protected IC. The low  $R_{DYN}$  of the triggered TVS holds this voltage ( $V_{CLAMP}$ ) to a safe level for the protected IC. For more information on how to properly use this device, refer to the [ESD Packaging and Layout Guide](#).

## 7 Device and Documentation Support

### 7.1 Documentation Support

#### 7.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [ESD Packaging and Layout Guide application reports](#)
- Texas Instruments, [ESD Layout Guide application reports](#)
- Texas Instruments, [Generic ESD Evaluation Module user's guide](#)
- Texas Instruments, [Picking ESD Diodes for Ultra High-Speed Data Lines application reports](#)
- Texas Instruments, [Reading and Understanding an ESD Protection data sheet](#)

### 7.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 7.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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### 7.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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### 7.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 7.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.



## 8 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Revision A (July 2023) to Revision B (July 2024)</b>	<b>Page</b>
• Added TSD36C to the data sheet.....	1
• Changed the status of the data sheet from: <i>Advanced Information</i> to: <i>Production Data</i> .....	1

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## 9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TSD05CDYFR	ACTIVE	SOT	DYF	2	3000	RoHS & Green	SN	Level-3-260C-168 HR	-40 to 125	33KF	<a href="#">Samples</a>
TSD36CDYFR	ACTIVE	SOT	DYF	2	3000	RoHS & Green	SN	Level-3-260C-168 HR	-55 to 150	3GNF	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TSD05CDYFR	SOT	DYF	2	3000	178.0	9.5	1.48	3.3	1.25	4.0	8.0	Q1
TSD36CDYFR	SOT	DYF	2	3000	178.0	9.5	1.48	3.3	1.25	4.0	8.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TSD05CDYFR	SOT	DYF	2	3000	210.0	200.0	42.0
TSD36CDYFR	SOT	DYF	2	3000	210.0	200.0	42.0

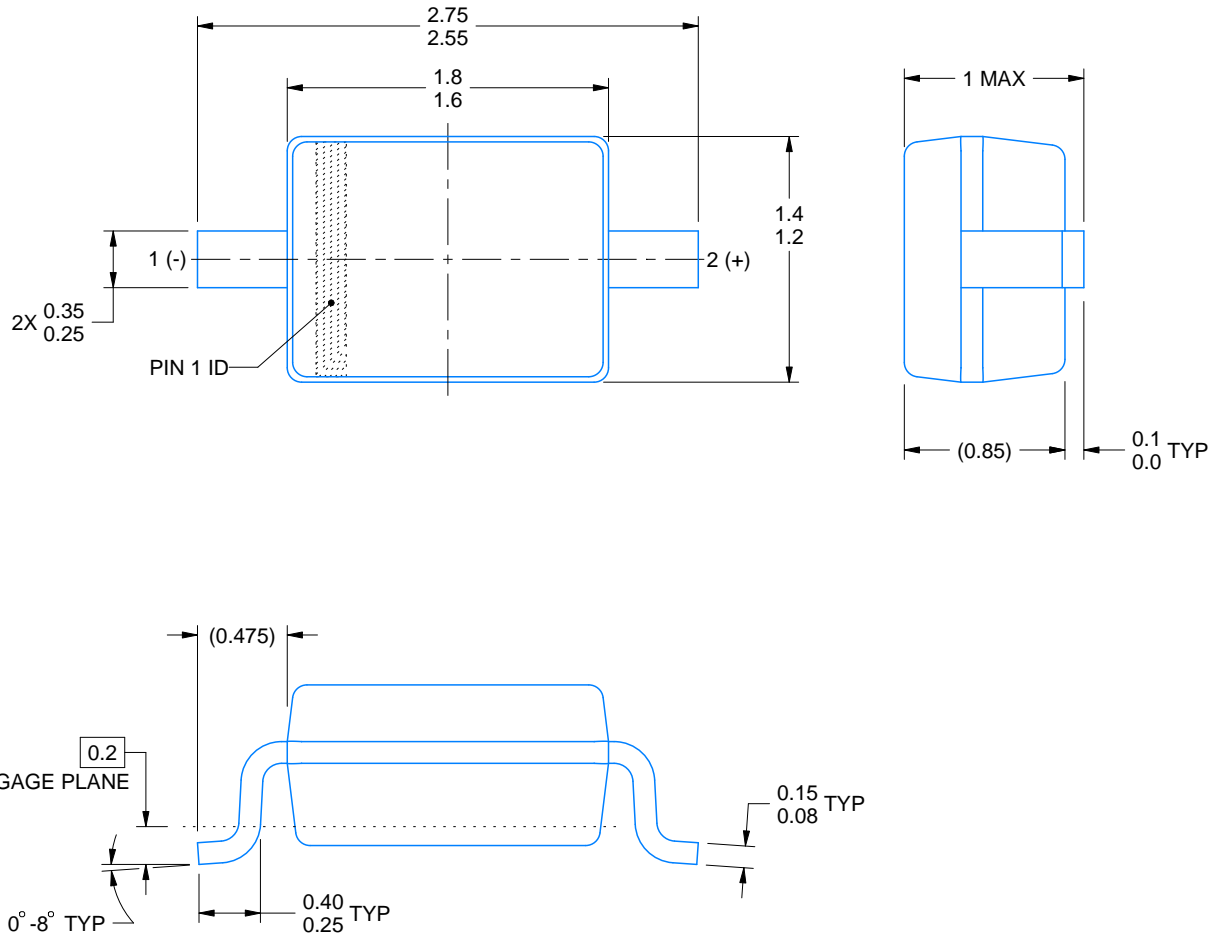
DYF0002A



# PACKAGE OUTLINE

SOT(SOD-323) - 1 mm max height

SMALL OUTLINE TRANSISTOR



4228484/A 02/2022

NOTES:

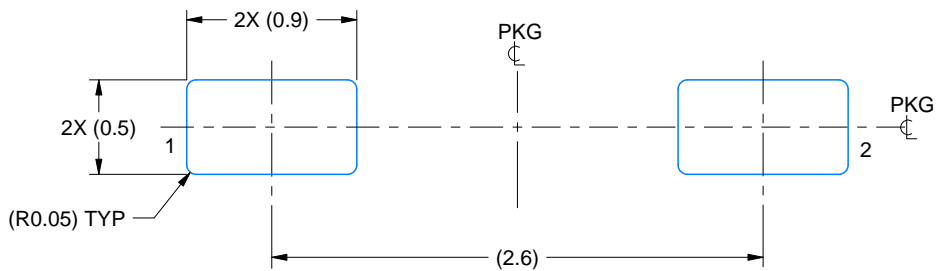
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

# EXAMPLE BOARD LAYOUT

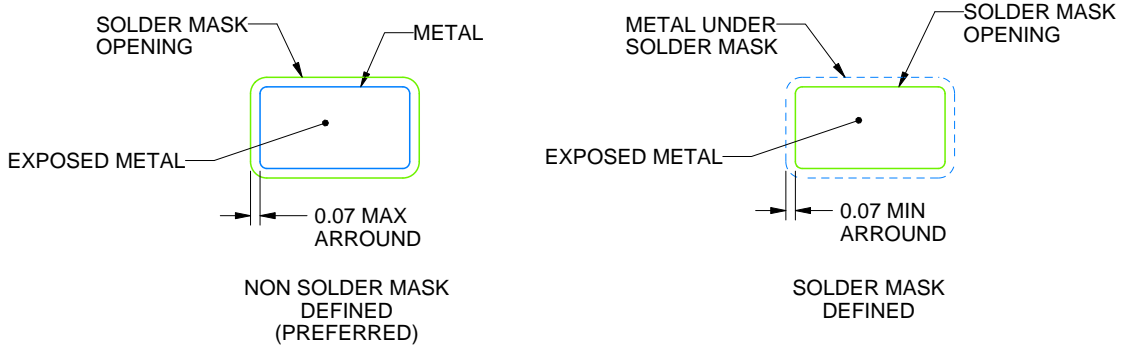
DYF0002A

SOT(SOD-323) - 1 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:25X



SOLDER MASK DETAILS

4228484/A 02/2022

NOTES: (continued)

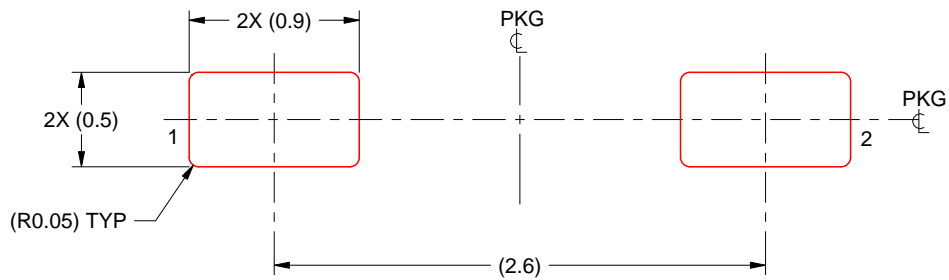
- 3. Publication IPC-7351 may have alternate designs.
- 4. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DYF0002A

SOT(SOD-323) - 1 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:25X

4228484/A 02/2022

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
6. Board assembly site may have different recommendations for stencil design.



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